

PHD9NQ20T

N-channel TrenchMOS standard level FET Rev. 03 — 16 December 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- DC-to-DC converters
- General purpose switching
- Motor control circuits

- Off-line switched-mode power supplies
- TV and computer monitor power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	200	V
I_D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V$	-	-	8.7	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	88	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A};$ $T_j = 25 \text{ °C}$	-	300	400	mΩ
Dynamic ch	naracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A};$ $V_{DS} = 160 \text{ V}; T_j = 25 \text{ °C}$	-	12	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	G	gate				
2	D	drain[1]	mb			
3	S	source				
mb	mb D mounting base; connected to dra	1 3	mbb076 S			
			SOT428 (DPAK)			

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHD9NQ20T	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	200	V
V_{GS}	gate-source voltage		-30	30	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C	-	6.2	Α
		V _{GS} = 10 V; T _{mb} = 25 °C	-	8.7	Α
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	35	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	88	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T _{mb} = 25 °C	-	8.7	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	35	Α
Avalanche r	uggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 7.2 A; V_{sup} ≤ 25 V; unclamped; t_p = 100 μ s; R_{GS} = 50 Ω	-	93	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V; } V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} $ $R_{GS} = 50 \Omega;$ unclamped	-	8.7	Α

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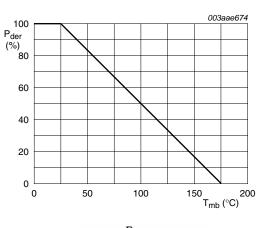
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N-channel TrenchMOS standard level FET

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$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature

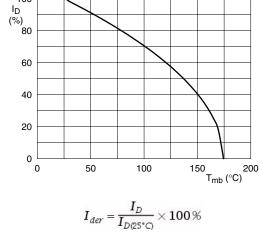
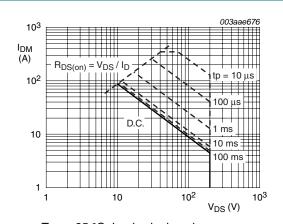


Fig 2. Normalized continuous drain current as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is single pulse Fig 3. Safe operating area; continuous and peak drain

currents as a function of drain-source voltage

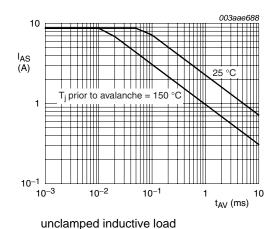


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

N-channel TrenchMOS standard level FET

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W

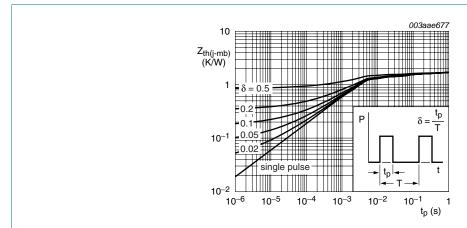


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
I_{DSS}	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A}; T_j = 175 \text{ °C}$	-	-	1.16	Ω
	resistance	$V_{GS} = 10 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$	-	300	400	mΩ
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 9 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$	-	24	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	4	-	nC
Q_{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	959	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	93	-	pF
C _{rss}	reverse transfer capacitance		-	54	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 100 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	19	-	ns
t _{d(off)}	turn-off delay time		-	25	-	ns
t _f	fall time		-	15	-	ns
9 _{fs}	transfer conductance	$V_{DS} = 25 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$	3.8	6	-	S
L _D	internal drain inductance	from tab to centre of die ; $T_j = 25$ °C	-	3.5	-	nΗ
L _S	internal source inductance	From source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 9 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	92	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.5	-	μC

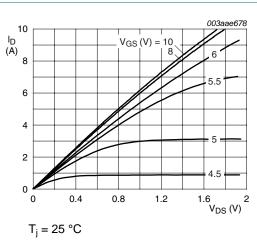


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

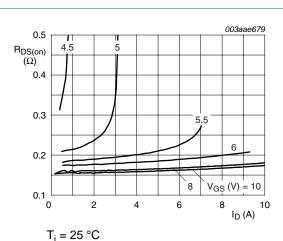


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

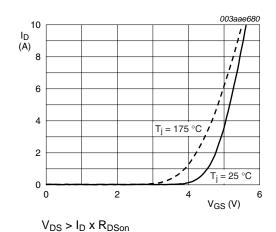


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

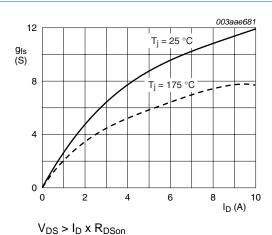


Fig 9. Forward transconductance as a function of drain current; typical values

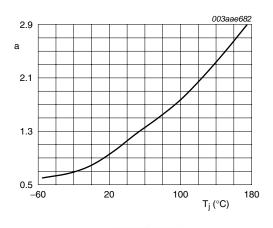
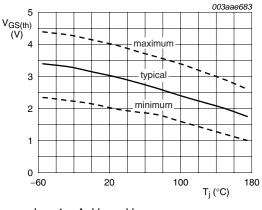


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature

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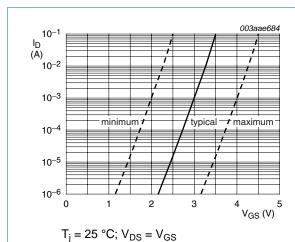


Fig 12. Sub-threshold drain current as a function of gate-source voltage

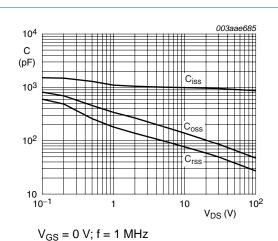


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

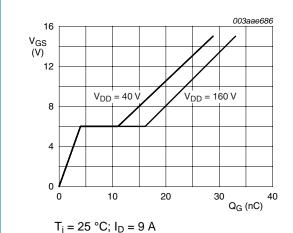
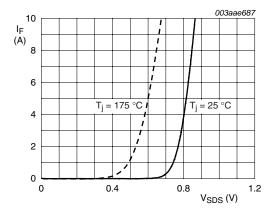


Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

Package outline

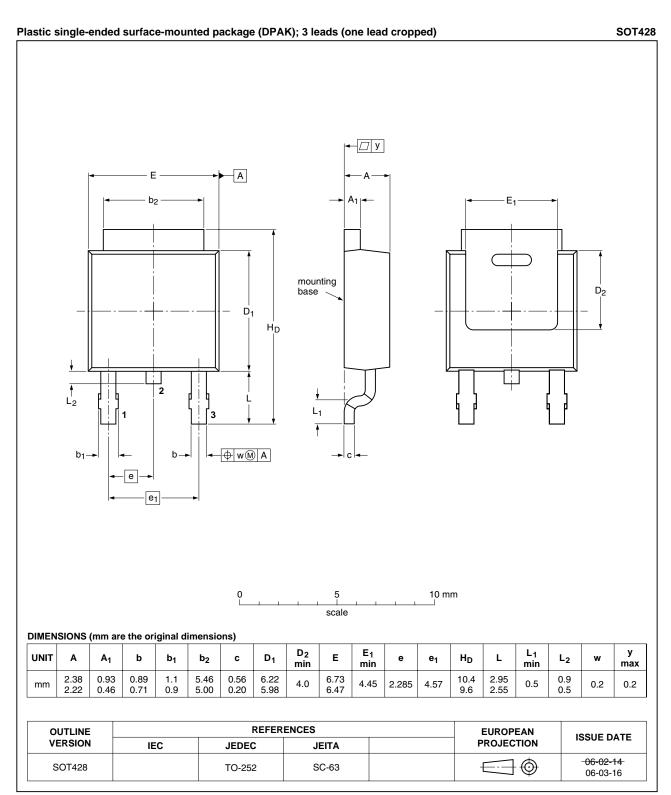


Fig 16. Package outline SOT428 (DPAK)

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N-channel TrenchMOS standard level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD9NQ20T v.3	20101216	Product data sheet	-	PHB_PHD_PHP9NQ20T v.2
Modifications:		of this data sheet has been of NXP Semiconductors.	en redesigned to co	mply with the new identity
	 Legal texts 	have been adapted to the	new company nan	ne where appropriate.
	 Type number 	er PHD9NQ20T separate	d from data sheet P	PHB_PHD_PHP9NQ20T v.2.
PHB_PHD_PHP9NQ20T v.2	20001001	Product specification	-	PHB_PHD_PHP9NQ20T v.1

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PHD9NQ20T

N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline
8	Revision history9
9	Legal information10
9.1	Data sheet status
9.2	Definitions10
9.3	Disclaimers
9.4	Trademarks
10	Contact information 11

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